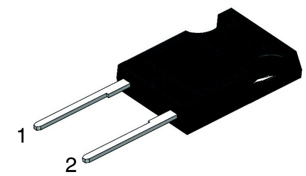
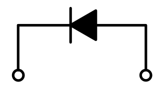
Silicon Carbide (SiC) Schottky Diode – EliteSiC, 40 A, 650 V, D1, TO-247-2L

FFSH4065A



TO−247−2LD
CASE 340CL



1. Cathode 2. Anode

Schottky Diode

MARKING DIAGRAM

A	= Assembly Plant Code
YWW	= Date Code (Year & Week)
KK	= Lot Traceability Code
FFSH4065A	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 182 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb−Free, Halogen Free/BFR Free and RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage		650	V
E_{AS}	Single Pulse Avalanche Energy (Note 1)		182	mJ
I_F	Continuous Rectified Forward Current @ T_C < 145°C		40	A
	Continuous Rectified Forward Current @ T_C < 135°C		48	A
$I_{F,\ Max}$	Non-Repetitive Peak Forward Surge Current	T_C = 25°C, 10 μs	1300	A
		T_C = 150°C, 10 μs	1200	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t_p = 8.3 ms	180	A
$I_{F,RM}$	Repetitive Forward Surge Current	Half-Sine Pulse, t_p = 8.3 ms	85	A
Ptot	Power Dissipation	T_C = 25°C	349	W
		T_C = 150°C	58	W
T_J, T_{STG}	Operating and Storage Temperature Range		–55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 182 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 27 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.43	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V_F	Forward Voltage	I_F = 40 A, T_C = 25°C	–	1.50	1.75	V
		I_F = 40 A, T_C = 125°C	–	1.60	2.0	
		I_F = 40 A, T_C = 175°C	–	1.72	2.4	
I_R	Reverse Current	V_R = 650 V, T_C = 25°C	–	–	200	μA
		V_R = 650 V, T_C = 125°C	–	–	400	
		V_R = 650 V, T_C = 175°C	–	–	600	
Q_C	Total Capacitive Charge	V = 400 V	–	119	–	nC
C	Total Capacitance	V_R = 1 V, f = 100 kHz	–	1989	–	pF
		V_R = 200 V, f = 100 kHz	–	218	–	
		V_R = 400 V, f = 100 kHz	–	164	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FFSH4065A	FFSH4065A	TO−247−2LD	30 Units / Tube

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

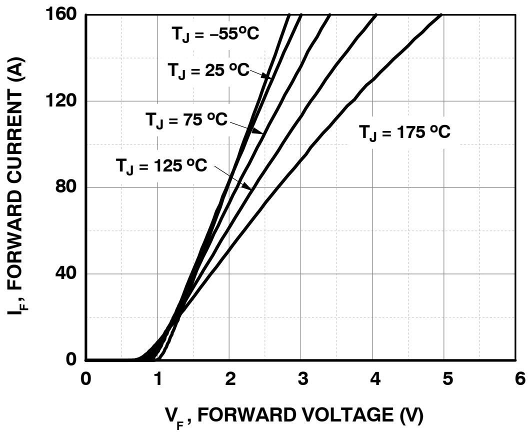


Figure 1. Forward Characteristics

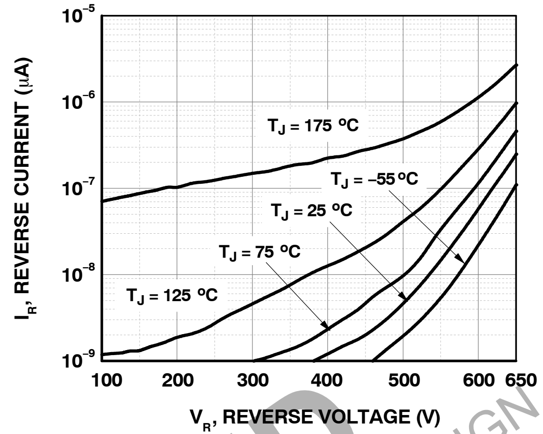


Figure 2. Reverse Characteristics

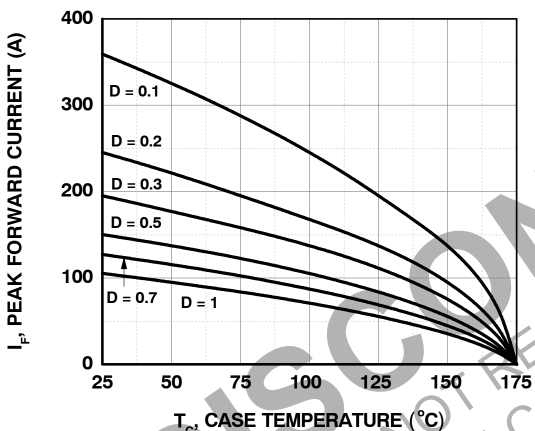


Figure 3. Current Derating

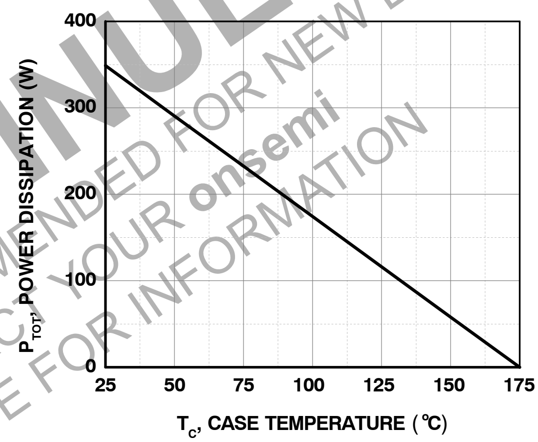


Figure 4. Power Derating

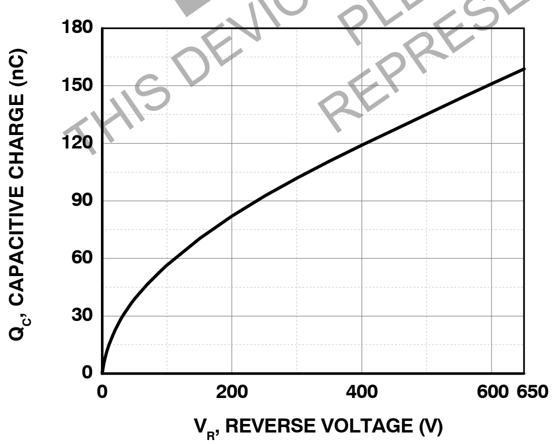


Figure 5. Capacitive Charge vs. Reverse Voltage

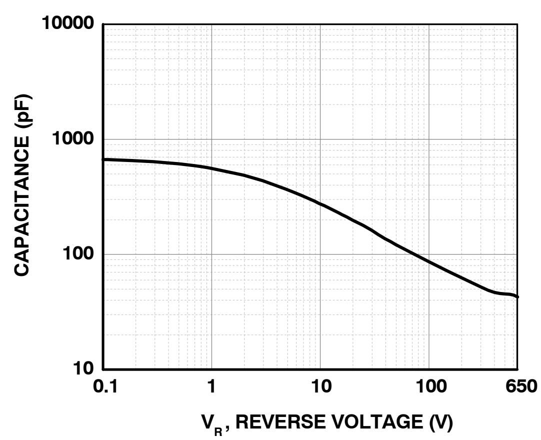


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

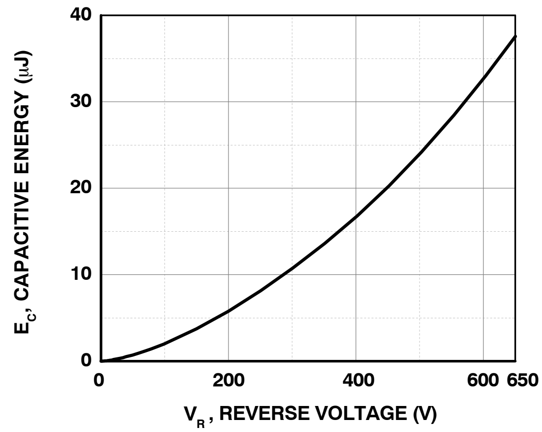


Figure 7. Capacitance Stored Energy

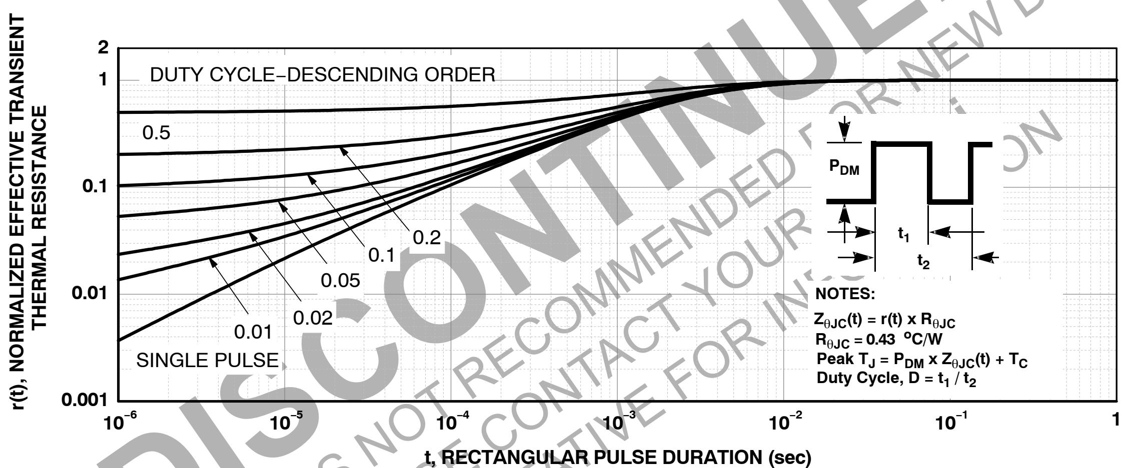


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

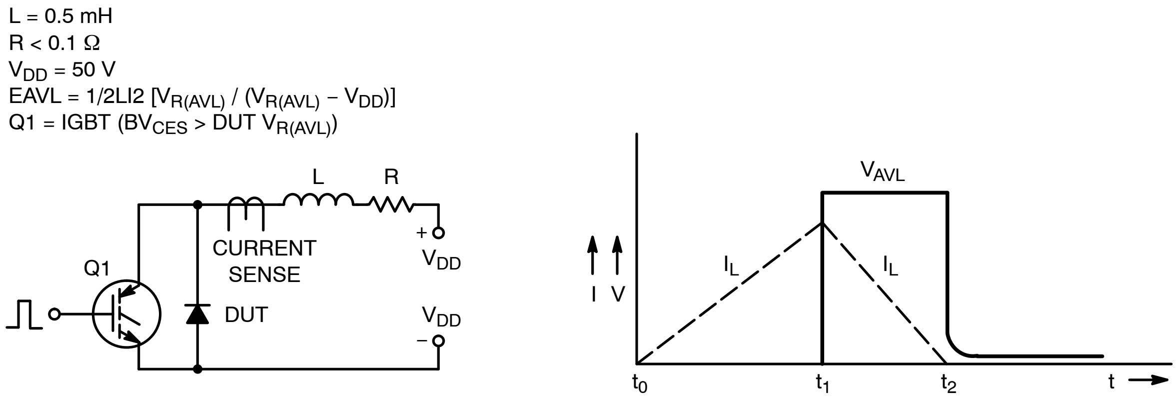


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

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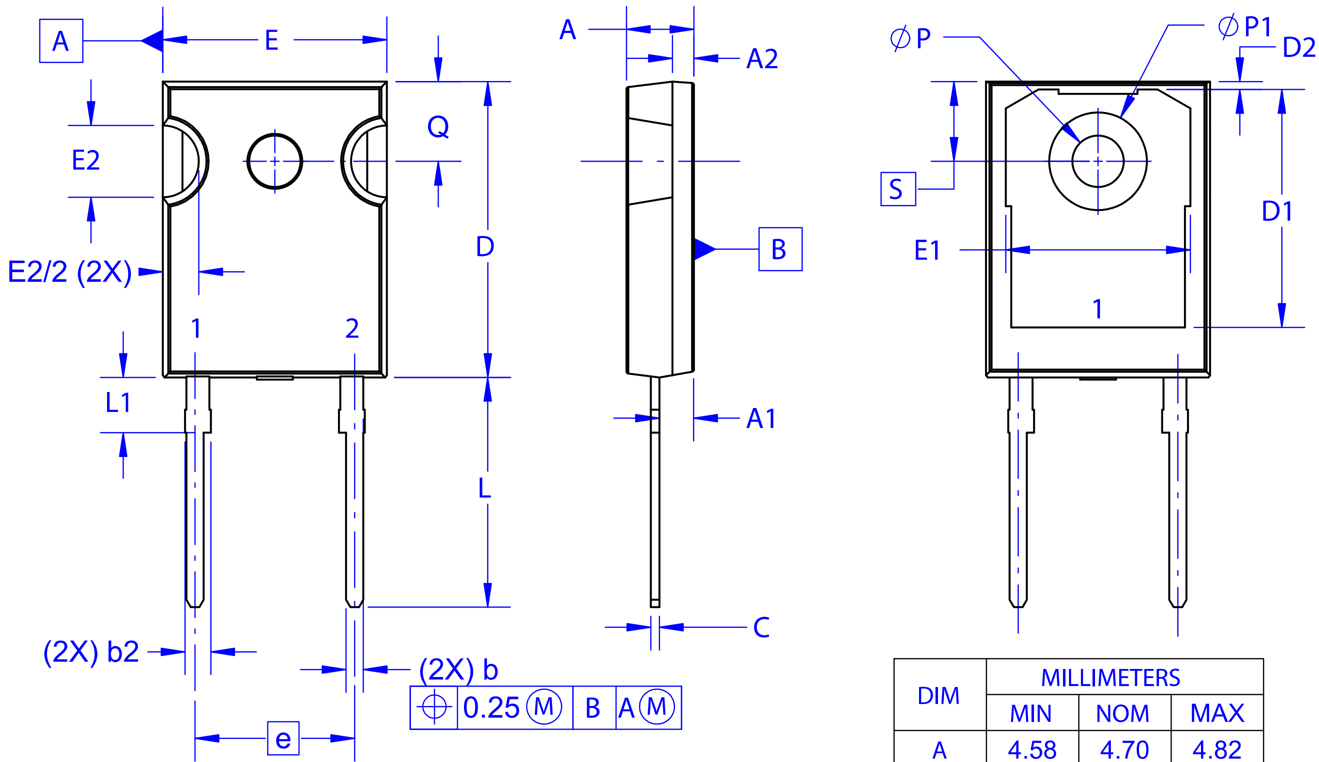
ISSUE A

DATE 03 DEC 2019

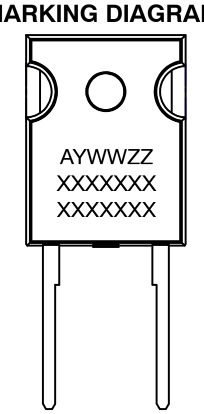


NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.29	2.40	2.66
A2	1.30	1.50	1.70
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	16.37	16.57	16.77
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	11.12	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
∅P	3.51	3.58	3.65
∅P1	6.61	6.73	6.85
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

GENERIC
MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**TO−247−2LD**	**PAGE 1 OF 1**

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